

C30902SH Series Avalanche Photodiode for Linear and Geiger Mode operation High Responsivity, Low Noise Reach-Through SPAD



Excelitas' C30902SH Avalanche Photodiodes are high speed, large area Silicon APDs that provide high responsivity at low noise. They are specially selected to be used either in Geiger Mode ($V_{op} > V_{BD}$) for detection of single photons or Linear Mode ($V_{op} < V_{BD}$) with Gains up to 250.

Key Features

- Spectral response 400 nm – 1100 nm
- Low Dark Current / Dark Count Rates
- High quantum efficiency of 84% at 800 nm
- SPAD for Photon Counting applications
- Large active area with diameter of 500 μm
- RoHS compliant

Applications

- LiDAR / ToF measurements
- Quantum Communication
- Optical time-domain reflectometer (OTDR)
- Laser scanning

All specifications are referring to an ambient temperature of $T_A = 22^\circ\text{C}$, $\lambda = 800\text{ nm}$ and a gain of $M = 250$ unless otherwise specified.

Table 1: Key parameters

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Breakdown Voltage	V_{BD}	185	225	260	V
Spectral Range	$\Delta\lambda$	400		1100	nm
Peak Responsivity	λ_{peak}		800		nm
Quantum Efficiency ¹	QE		84		%

Note 1: Quantum Efficiency is not a directly measureable quantity. The above specified typical parameter is linked to the typical responsivity by $QE = \frac{1240R}{\lambda M}$

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Table 2: Ordering Information

Parameter	C30902SH	C30902SH-2	C30902SH-TC	C30902SH-DTC
Reach-Through APD			X	
Geiger Mode SPAD ¹			X	
Flat Glass Window			X	
Active Area Shape			Circular	
Useful Area			0.2 mm ²	
Useful Diameter			0.5 mm	
905 nm Filter		X		
Single Stage TEC ^{2,4}			X	
Double Stage TEC ^{3,4}				X
TO-18 package	X	X		
TO-66 flange outline package			X	X

Note 1: This APD is suitable for low-noise operation in linear mode or photon counting in the Geiger mode.

Note 2: The recommended APD operating temperature of the single stage TEC is typically 0 °C.

Note 3: The recommended APD operating temperature of the double stage TEC is typically -20 °C.

Note 4: Adding a TEC to the APD will significantly reduce dark current, dark noise and NEP.

Table 3: Absolute Maximum Ratings

Parameter	Symbol	Condition	Value	Units
Forward Current	I _F	RMS	5	mA
		Single Peak, 1 s	50	
Total Power dissipation	P _{tot}		60	mW
Reverse Current	I _R	RMS	0.2	mA
		Single Peak, 1s	1	
Drive Current TEC	I _{-TC}	RMS	1.8	A
	I _{-DTC}		1.4	
Bias Voltage TEC	V _{-TC}	RMS	0.8	V
	V _{-DTC}		2	
Storage Temperature	T _S		-60 ... 100	°C
Operating Temperature	T _{Op}		-40 ... 85	

Note 1: Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device.

Note 2: Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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Table 4: Electrical Specifications Linear Mode

Parameter	Symbol	Minimum	Typical	Maximum	Units
Recommended Operating Gain	M		250		
Responsivity	R	117	135		A/W
Rise Time / Fall Time ¹	t_r / t_f		0.4		ns
Bandwidth	f_{3dB}		800		MHz
Temperature Coefficient of V_{BD}	$\Delta V / \Delta T$	0.5	0.7	0.9	V/°C
Capacitance	C		1.5	1.8	pF
Dark Current ²	i_D		7	10	nA
	$i_{D,TC}$		2		
	$i_{D,DTC}$		1		
Dark Noise ³	i_N		0.1	0.25	pA/√Hz
	$i_{N,TC}$		0.04		
	$i_{N,DTC}$		0.02		
Noise Equivalent Power ⁴	NEP		0.74		fW/√Hz
	NEP_{TC}		0.29		
	NEP_{DTC}		0.15		

Note 1: As estimated by $t_{r/f} = \frac{0.35}{f_{3dB}}$

Note 2: Surface (i_{DS}) and bulk (i_{DB}) dark current are contributing to the total dark current by
 $i_D = i_{DS} + i_{DB}M$.

Note 3: Due to the natural fluctuations of amplified charge carriers the APD will also generate noise when not illuminated. Since the noise characteristics and hence the signal-to-noise ratio (SNR) are depending on the bandwidth (B) and used wavelength (λ) inside the final system the illuminated noise

$$i_{ill} = \sqrt{2qB[i_{DS} + (i_{DB}M^2 + R_0(\lambda)M^2P)F]}$$

needs to be considered. Hence the SNR defines as: $SNR = \frac{i_P^2}{i_{ill}^2} = \frac{(PR_0(\lambda)M)^2}{i_{ill}^2}$ with P the incident optical power in W, $R_0(\lambda)$ the intrinsic ($M = 1$) responsivity in A/W, q the charge carrier and F the excess noise factor (ENF).

It is not recommended to use approximations like $F = M^x$ as this method gives erroneously results versus actual measurements of an APD, particularly when operated at gains that are differing from the specified gain in the datasheet. The ENF at a certain gain is depending on the k-factor k_{eff} , a material property of the APD, which for the C30902SH series is $k_{eff} = 0.02$.

For more information see also :

Philippe Bérard, Martin Couture, and Richard J. Seymour "Excess noise factor of front and back-illuminated silicon avalanche photodiode", Proc. SPIE 11388, Image Sensing Technologies: Materials, Devices, Systems, and Applications VII, 113880P (23 April 2020)

$$F(M, k_{eff}) = k_{eff}M + (2 - \frac{1}{M})(1 - k_{eff})$$

Note 4: The NEP is specified in dark conditions as $NEP = \frac{i_N}{R(\lambda, M)}$

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Table 5: Optical Specifications C30902SH-2

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Spectral Range	$\Delta\lambda_{905}$	860		960	nm
Responsivity ¹	R_{905}	90	110		A/W
Peak Responsivity	$\lambda_{peak,905}$		905		nm
Quantum Efficiency ¹	QE_{905}		60		%

Note 1: At $\lambda = 905$ nm

Table 6: Electrical Specifications Geiger Mode

Parameter	Symbol	Minimum	Typical	Maximum	Units
Recommended Overvoltage	ΔV		20		V
Photon Detection Efficiency ¹	PDE		53		%
Dark Count Rate	DCR		20	80	kcps
	DCR_{TC}		3.3	12	
	DCR_{DTC}		0.6	3	
After-pulse ratio ^{2,3}	APR		3	10	%

Note 1: The C30902SH can be operated at a substantially higher PDE, refer to Figure 9.

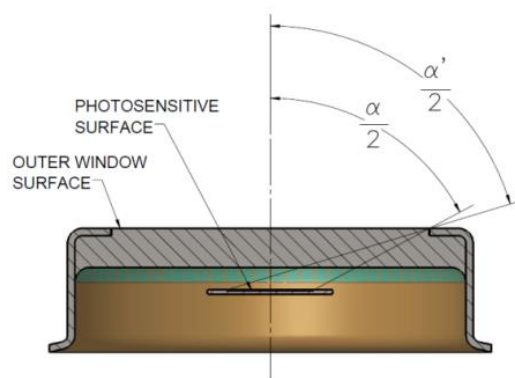
Note 2: After-pulse is strongly dependent on the read-out circuitry used.

Note 3: Measured with an active quenching circuit with a dead-time of 100 ns.
The after pulse is measured from 100 ns to 500 ns.

Table 7: Aperture Specifications

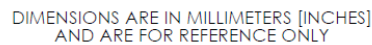
Parameter	C30902SH	C30902SH-2	C30902SH-TC, C30902SH-DTC	Units
Field of view α	90	55	122	°
Field of view α'	114	78	129	°

Figure 1: Field of view definition



VS-383

Figure 2: TO-18 Dimensions C30902SH



Technical drawing of a photodiode showing three views: top, side, and perspective.

Top View Dimensions:

- Overall diameter: $\phi 5.41 [.213]$

Side View Dimensions:

- Overall length: $5.23 [.206]$
- Internal diameter: $\phi 4.70 [.185]$
- Photodiector reference plane to end of body: $2.32 [.091]$
- Distance from reference plane to anode/cathode leads: $12.7 [.50] \text{ MIN}$
- Anode (-) and Cathode (+) leads
- Lead diameter: $2 \times \phi 0.44 [.018]$
- Lead length: $1.27 [.050]$

Perspective View:

- Shows the cylindrical body and the two leads.

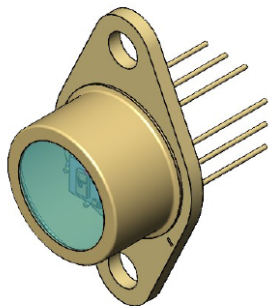
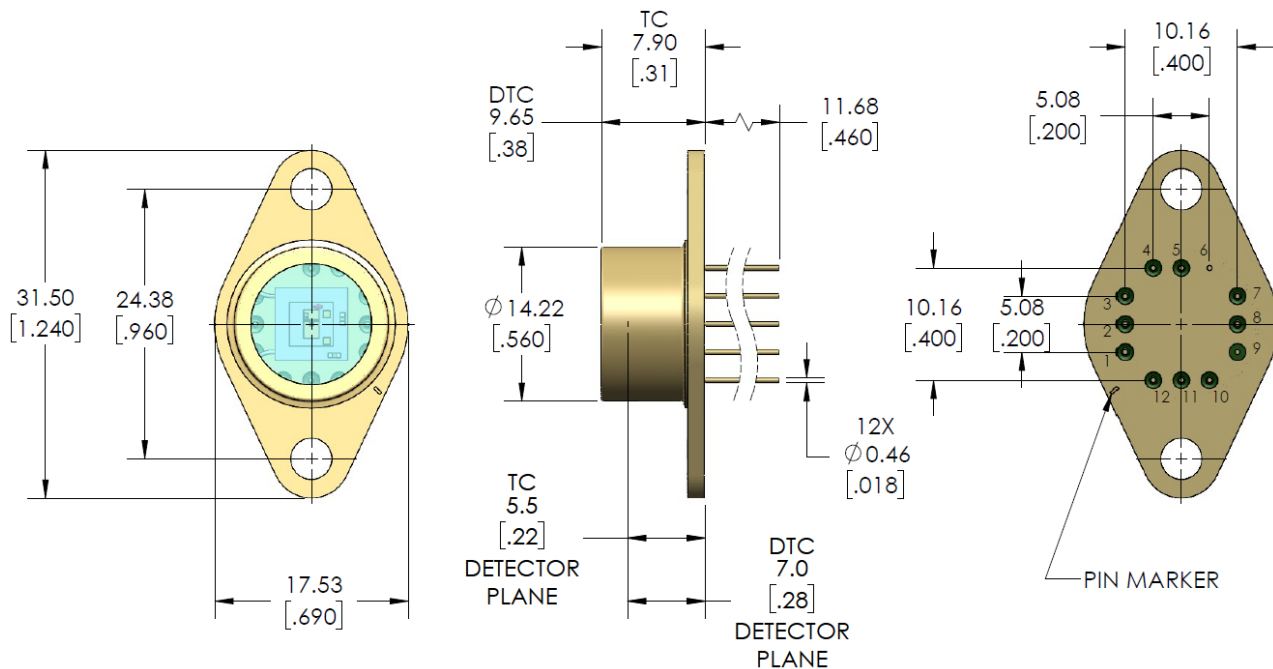
Dimensions are in millimeters [inches] and are for reference only.

DIMENSIONS ARE IN MILLIMETERS [INCHES]
AND ARE FOR REFERENCE ONLY

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Figure 4: TO-66 Dimensions C30902SH-TC, C30902SH-DTC



PINOUT	
1	NC
2	DETECTOR ANODE
3	NC
4	THERMISTOR
5	THERMISTOR
6	CASE/GND
7	COOLER-
8	N/C
9	COOLER+
10	N/C
11	N/C
12	DETECTOR CATHODE

DIMENSIONS ARE IN MILLIMETERS [INCHES]
AND ARE FOR REFERENCE ONLY

Note 1: The temperature of the Thermistor in Kelvin can be calculated using the following equation:

$$[K] = \frac{\beta}{\ln \left(\frac{R}{r_{\infty}} \right)}$$

where R is the measured Thermistor resistance in Ω , $\beta = 3200$, $R_0 = 5100 \Omega$, $r_{\infty} = R_0 e^{-\frac{\beta}{T_0}}$ and $T_0 = 298.15 \text{ K}$

Note 2: It is recommended to use a PID regulator to operate the TEC.

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Figure 5: Typical Responsivity

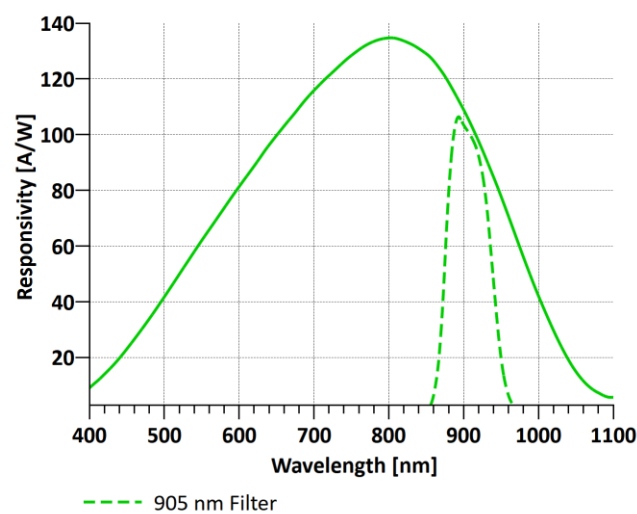


Figure 6: Typical Quantum Efficiency

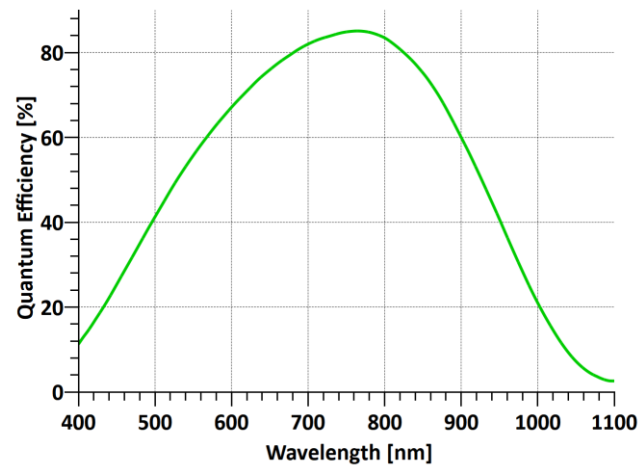


Figure 7: Typical Capacitance

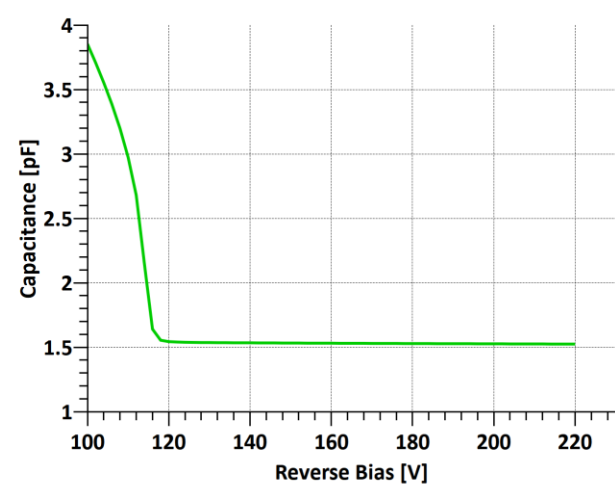
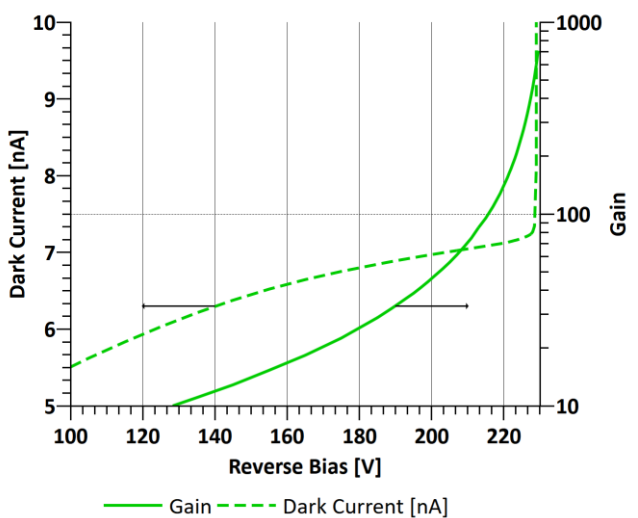


Figure 8: Typical Dark Current and Gain



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Figure 9: Typical PDE and APR

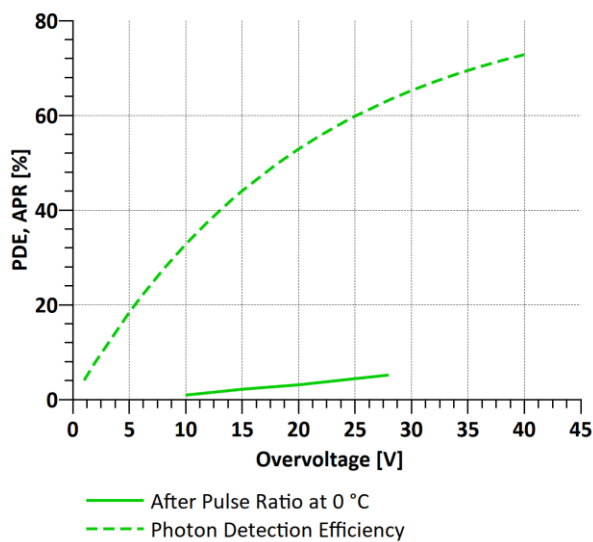


Figure 10: Typical Noise Parameter

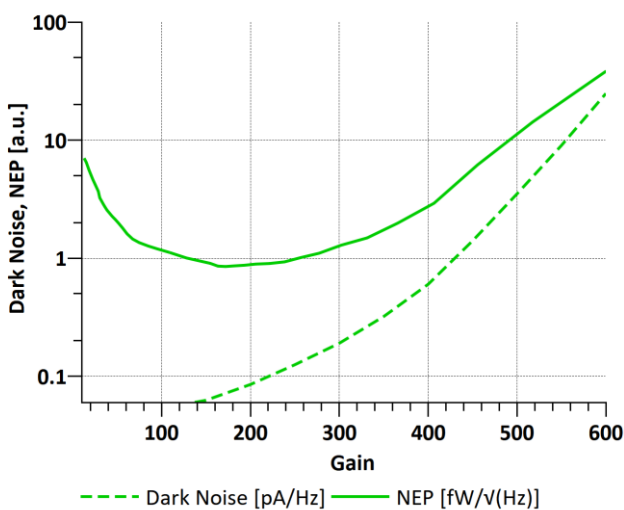


Figure 11: Typical Dark Count Rate

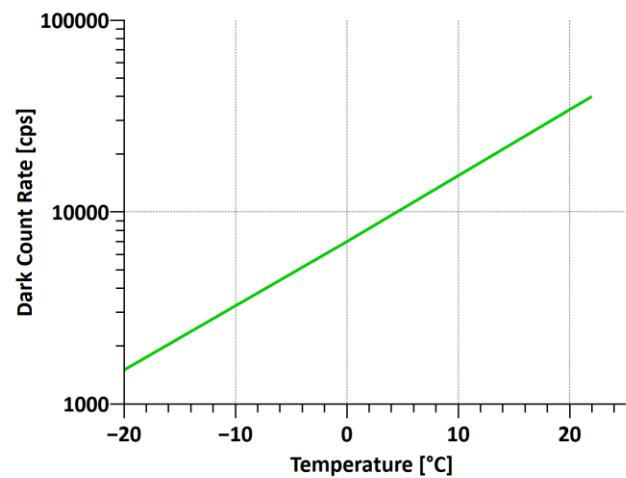
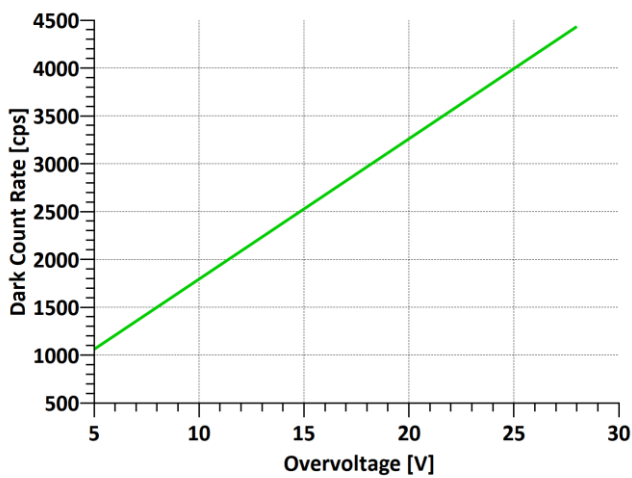


Figure 12: Typical Dark Count Rate at 0°C



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Information

Excelitas' C30902SH family of Silicon SPADs provide extremely low noise and bulk dark-current enabling very high performance data and distance measurements. They are especially well suited for ultra-low light level detection applications (e.g. single photon counting and quantum communication) and intended for use with optical powers less than 1 pW. The C30902SH can be used in either the linear mode ($V_{OP} < V_{BD}$) at typical gains of 250 or greater, or in "Geiger" mode ($V_{OP} > V_{BD}$) with extremely low and stable dark count rates and after pulsing ratios. In this mode, no amplifiers are necessary and single-photon detection probabilities of up to approximately 50% are possible. For even greater performance, these high performance SPADs are available with single or dual-stage thermoelectric coolers.

The responsivity of the APD is independent of modulation frequency up to about 800 MHz. The detector chip is hermetically-sealed behind a flat glass window in a TO-18 package, or TO-66 flange outline when ordered with a TEC. The useful diameter of the photosensitive surface is 0.5 mm.

Thermo-Electric-Cooled Version

TE cooled APDs can be used for multiple reasons. Most applications benefit from using a cooled APD for two reasons:

- To reduce the thermal noise for very small signal detection
- To keep a constant APD temperature at varying ambient temperatures. As the APD breakdown voltage decreases with a decrease in temperature, the TE cooler allows a single operating voltage and hence a constant APD performance over an extended ambient temperature range.

The thermistor located inside the package can be used to monitor the APD temperature, to implement a feedback loop to keep the APD chip at a constant temperature and/or to implement a temperature compensation on the APD bias voltage. A proper heat-sink is required to dissipate the heat generated by the APD and the TE cooler.

Geiger Mode Operation

When biased above the breakdown voltage, an avalanche photodiode will normally conduct a large current. However, if the current is limited to less than a particular value (about 50 μ A for these diodes), the current is unstable and can switch off by itself using either "passive" or "active" pulse quenching circuits. Each circuit has application specific (dis-)advantages and hence a detailed description is omitted here.

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Testing methods

Excelitas verifies the electro optical specifications on every device. Hence, a specific voltage, V_{OP} , is supplied with each device. When the photodiode is operated at this voltage (at 22 °C), it will meet the electrical specifications shown above. This voltage will be lower than the breakdown voltage V_{BD} .

Visual inspection during fabrication is performed as per our quality standard and failed diodes are removed. Excelitas Technologies is certified to meet ISO-9001 and are designed to meet MIL-STR-883 and/or MIL-STD-750 specifications.

The following parameters are part of Excelitas testing procedures

- Operating Voltage
- Breakdown Voltage
 - o C30902SH-TC: additionally at 0 °C
 - o C30902SH-DTC: additionally at -20 °C
- Dark Current
- Responsivity @ 830 nm
- Dark Noise
- Geiger Mode Voltage
- Photon Detection Efficiency
- Dark Count Rate

Packaging and shipping

The C3902SH series APDs are shipped in ESD safe plastic trays.

Storage and handling

Excelitas highly recommends to follow the below notes:

- Keep APDs in a ESD controlled environment until final assembly.
- Keep the trays closed until final assembly.
- Remove APDs from tray by using a non-metallic, ESD safe tweezer.

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RoHS Compliance

This series of APD diodes are designed and built to be fully compliant with the European Union Directive on restrictions of the use of certain hazardous substances in electrical and electronic equipment.



Warranty

A standard 12-month warranty following shipment applies.

About Excelitas Technologies

Excelitas Technologies is a global technology leader focused on delivering innovative, customized solutions to meet the lighting, detection and other high-performance technology needs of OEM customers.

Excelitas has a long and rich history of serving our OEM customer base with optoelectronic sensors and modules for more than 45 years beginning with PerkinElmer, EG&G, and RCA. The constant throughout has been our innovation and commitment to delivering the highest quality solutions to our customers worldwide.

From aerospace and defense to analytical instrumentation, clinical diagnostics, medical, industrial, and safety and security applications, Excelitas Technologies is committed to enabling our customers' success in their specialty end-markets. Excelitas Technologies has approximately 7,000 employees in North America, Europe and Asia, serving customers across the world.

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